

Amendments to the Specification:

Please replace paragraph [0045] with the following amended paragraph:

**[0045]** The ILD-0/1 layer is to be lithographically patterned. However, when a photoresist layer such as 280 is exposed to mask-patterned radiation (e.g., UV light), undesired reflections may be produced by reflective surfaces (e.g., silicon) below the photoresist layer. It is therefore common to provide an Anti-Reflection Coating (ARC) layer 270 immediately below the photoresist layer. The ARC layer may be composed of any one of a variety of organic compounds that absorb light at wavelengths such as those used for imaging the overlying photoresist layer 280. ~~Examples include SiON, Si<sub>3</sub>N<sub>4</sub>, or mixtures of these or of other such organic compositions.~~ In one embodiment, the organic ARC layer 270 typically has a thickness of about 100Å to 1000Å or more. In one embodiment, the ARC layer has a thickness of about 700Å to 800Å (about 750Å as an average). The overlying photoresist layer 280 may be composed of a UV-sensitive photoresist material such as UV6 and may have a thickness of about 0.61µm or less. Both the PR layer 280 and the ARC layer may be stripped away by plasma volatilization after they are no longer useful.